

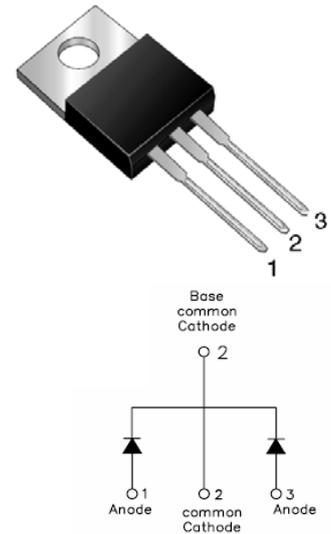
MBR60150CT SCHOTTKY RECTIFIER

Applications:

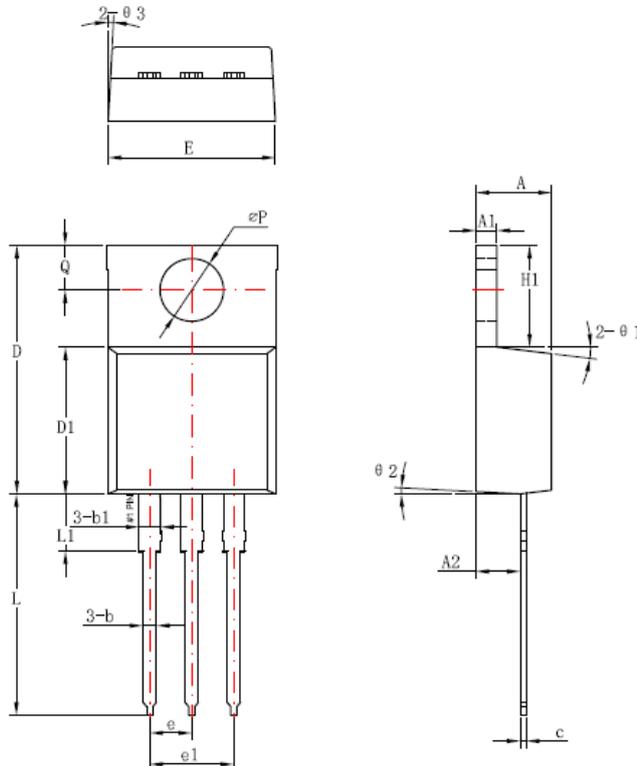
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 175 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

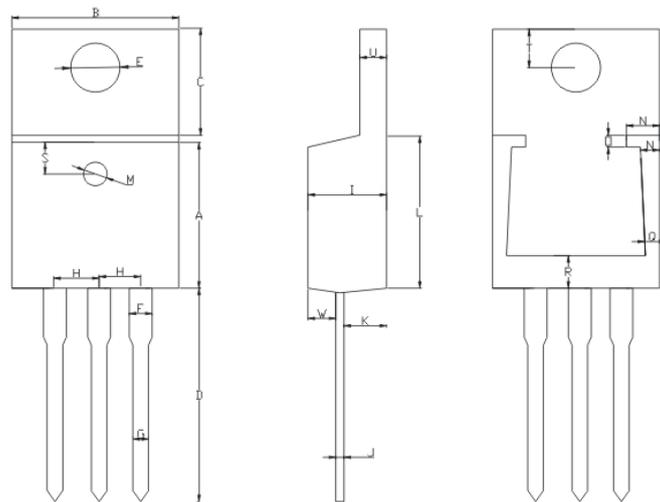


Mechanical Dimensions: In mm



Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
θ1		7°	
θ2		3°	
θ3		4°	

OPTION 1(HD)



A: 8.5±0.5	B: 9.5±0.5	C: 6.4±0.5	D: 14.1±1
E: 3.84±0.03	F: 1.27±0.03	G: 0.85±0.10	H: 2.54±0.025
I: 4.6±0.5	J: 0.38±0.015	K: 2.75±0.025	L: 9.0±0.5
M: 1.5±0.05	N: 1.8±0.05	O: 0.5±0.05	P: 1.2±0.05
Q: 0.9±0.05	R: 3.2±0.05	S: 1.55±0.05	T: 2.8±0.15
U: 1.27±0.05	W: 1.27±0.03		

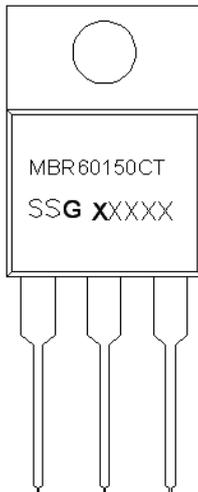
OPTION 2(SR)

TO-220AB

Technical Data
Data Sheet N0778, Rev. -

Green Products

Marking Diagram:



Where XXXXX is YYWWL

MBR = Device Type
60 = Forward Current (60A)
150 = Reverse Voltage (150V)
CT = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBR60150CT	TO-220AB (Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Average Forward Current(per device)	$I_{F(AV)}$	50% duty cycle @ $T_C = 150^\circ\text{C}$, rectangular wave form	60	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	270	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop (per leg) *	V_{F1}	@30A, Pulse, $T_J = 25\text{ }^\circ\text{C}$	0.94	V
	V_{F2}	@30A, Pulse, $T_J = 125\text{ }^\circ\text{C}$	0.76	V
Reverse Current (per leg) *	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	10	mA

* Pulse Width < 300 μ s, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +175	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{th(j-c)}$	DC operation	1.0(per leg)	$^\circ\text{C/W}$
			0.7(per device)	
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			

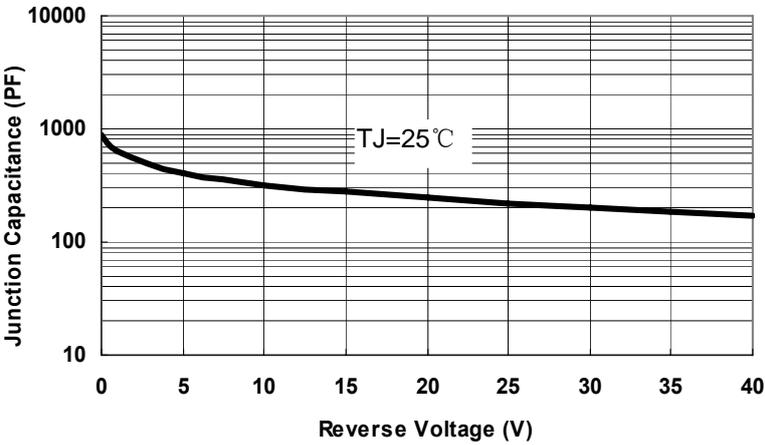


Fig.1-Typical Junction Capacitance

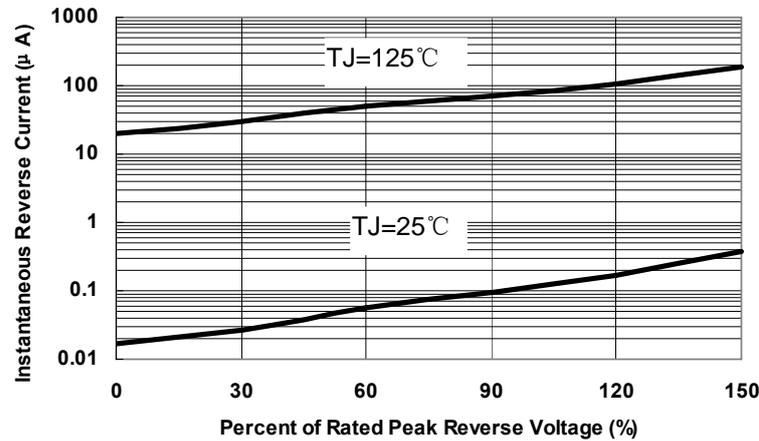


Fig.2-Typical Reverse Characteristics

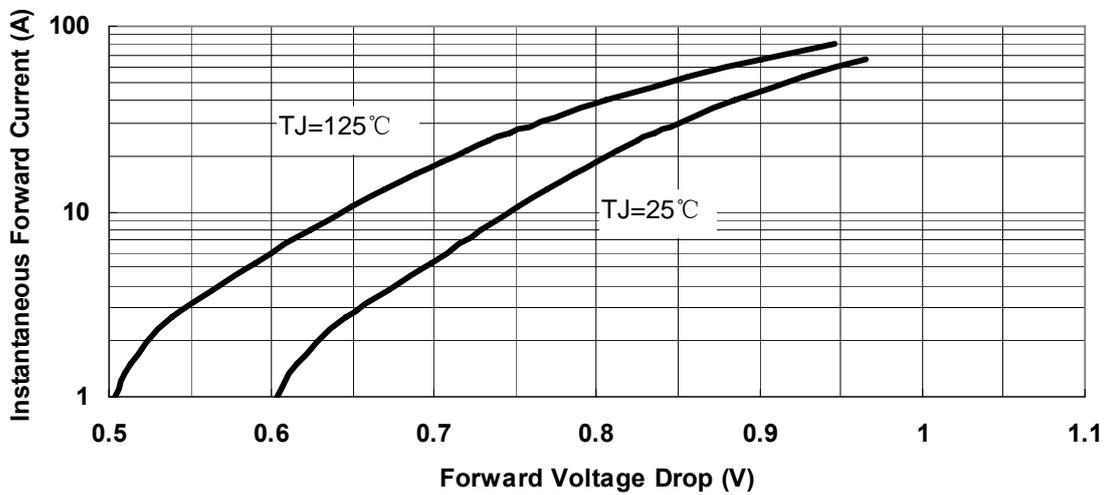


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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